

# INA1001AC1-TH50

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION  
SILICON PNP EPITAXIAL TYPE

AEC-Q101 Compliance

## DESCRIPTION

INA1001AC1 is a silicon PNP epitaxial type transistor.  
It is designed with high collector current and small  $V_{CE(sat)}$ .

## FEATURE

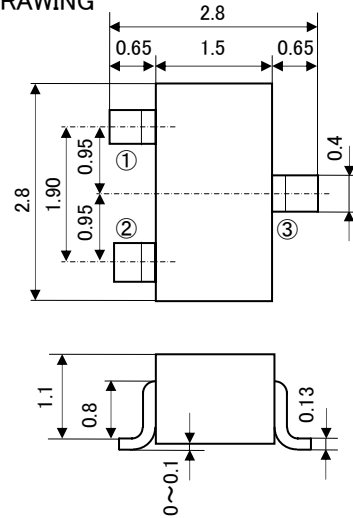
- Super mini package for easy mounting
- High collector current ( $I_C = -500\text{mA}$ )
- Low collector saturation voltage  
( $V_{CE(sat)} < -0.3V_{max}$ ;  $I_C = -100\text{mA}$ ,  $I_B = -10\text{mA}$ )
- High voltage  $V_{CEO} = -80\text{V}$

## APPLICATION

Power supply, Relay drive

## OUTLINE DRAWING

UNIT: mm



Terminal Connector

JEITA:SC-59

①: Base

JEDEC: Similar to TO-236

②: Emitter

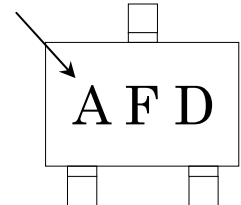
③: Collector

## MAXIMUM RATING ( $T_a = 25^\circ\text{C}$ )

| SYMBOL    | PARAMETER                                          | RATING     | UNIT             |
|-----------|----------------------------------------------------|------------|------------------|
| $V_{CBO}$ | Collector to Base voltage                          | -80        | V                |
| $V_{EBO}$ | Emitter to Base voltage                            | -4         | V                |
| $V_{CEO}$ | Collector to Emitter voltage                       | -80        | V                |
| $I_C$     | Collector current                                  | -500       | mA               |
| $P_C$     | Collector dissipation ( $T_a = 25^\circ\text{C}$ ) | 200        | mW               |
| $T_j$     | Junction temperature                               | +150       | $^\circ\text{C}$ |
| $T_{stg}$ | Storage temperature                                | -55 ~ +150 | $^\circ\text{C}$ |

## MARKING

Type Name



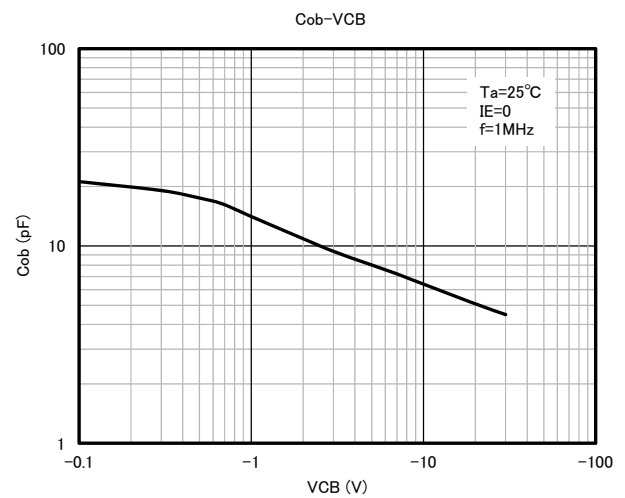
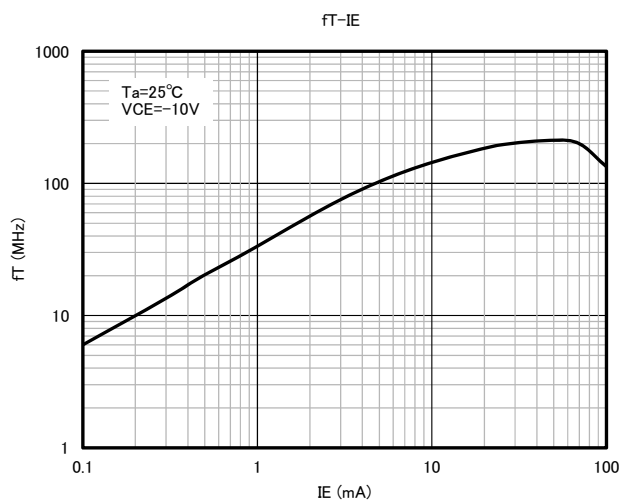
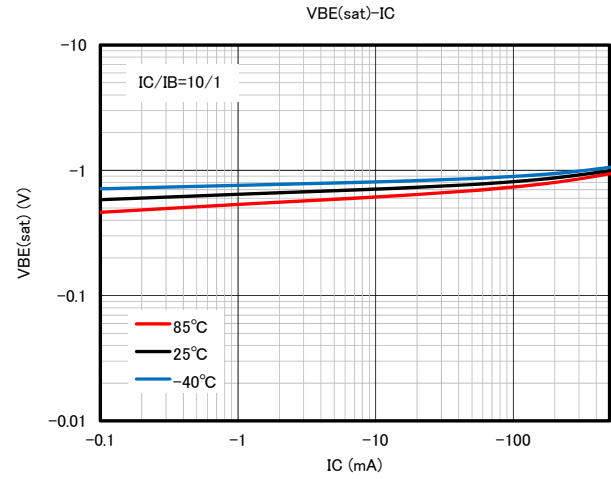
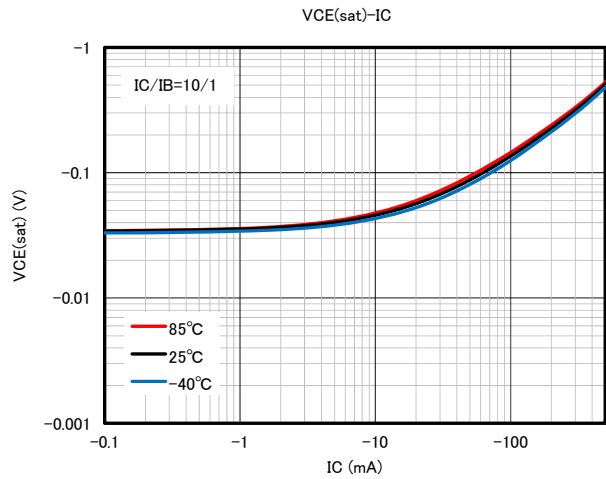
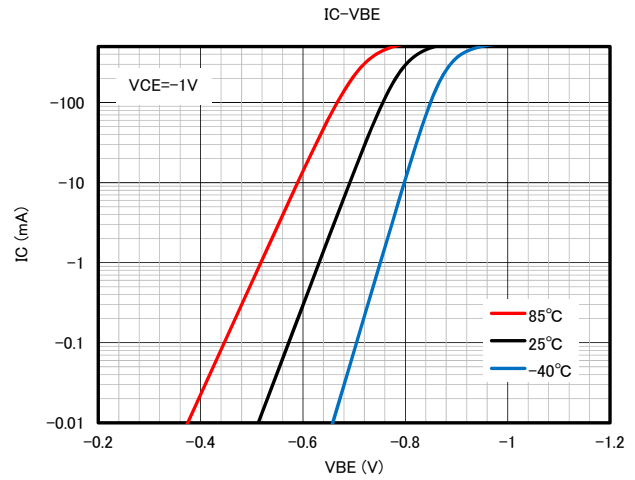
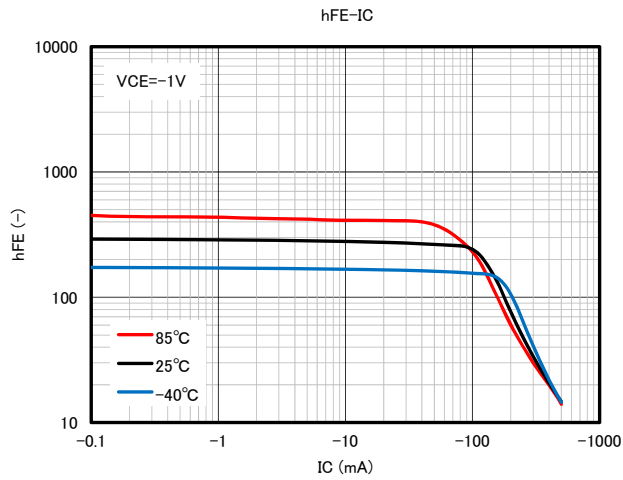
## ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

| SYMBOL        | PARAMETER                 | TEST CONDITIONS                                                    | LIMITS |     |      | UNIT          |
|---------------|---------------------------|--------------------------------------------------------------------|--------|-----|------|---------------|
|               |                           |                                                                    | MIN    | TYP | MAX  |               |
| $V_{(BR)CBO}$ | C to B breakdown voltage  | $I_C = -100\mu\text{A}$ , $I_E = 0\text{mA}$                       | -80    | -   | -    | V             |
| $V_{(BR)EBO}$ | E to B breakdown voltage  | $I_E = -100\mu\text{A}$ , $I_C = 0\text{mA}$                       | -4     | -   | -    | V             |
| $V_{(BR)CEO}$ | C to E breakdown voltage  | $I_C = -1\text{mA}$ , $I_B = 0\text{mA}$                           | -80    | -   | -    | V             |
| $I_{CBO}$     | Collector cut off current | $V_{CB} = -80\text{V}$ , $I_E = 0\text{mA}$                        | -      | -   | -0.1 | $\mu\text{A}$ |
| $I_{EBO}$     | Emitter cut off current   | $V_{EB} = -4\text{V}$ , $I_C = 0\text{mA}$                         | -      | -   | -0.1 | $\mu\text{A}$ |
| $h_{FE1}$     | DC forward current gain1  | $V_{CE} = -1\text{V}$ , $I_C = -10\text{mA}$                       | 95     | -   | -    | -             |
| $h_{FE2}$     | DC forward current gain2  | $V_{CE} = -1\text{V}$ , $I_C = -100\text{mA}$                      | 95     | -   | -    | -             |
| $V_{CE(sat)}$ | C to E saturation voltage | $I_C = -100\text{mA}$ , $I_B = -10\text{mA}$                       | -      | -   | -0.3 | V             |
| $f_T$         | Gain bandwidth product    | $V_{CE} = -1\text{V}$ , $I_E = 100\text{mA}$ , $f = 100\text{MHz}$ | 50     | -   | -    | MHz           |

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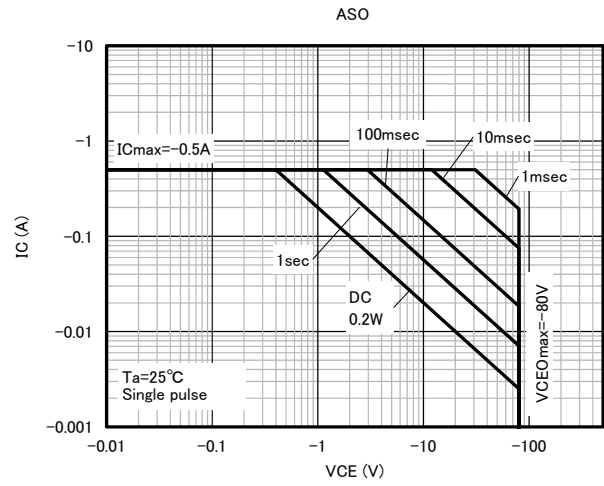
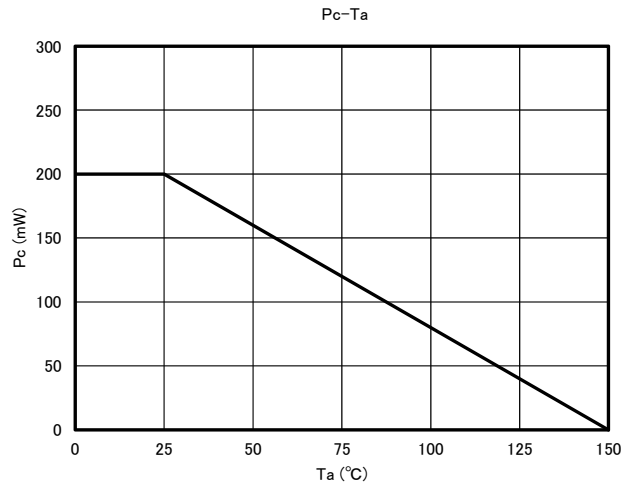
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## TYPICAL CHARACTERISTICS



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